DFS900HF12I4C1

1200V/900A Half Bridge SiC MOSFET Module

Description

The DFS900HF12I4C1 is a Half Bridge SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Motor drives and Renewable energy.

Features

- Blocking voltage 1200V
- $R_{DS(on)}$ =3.0mΩ
- Low thermal resistance with Si_3N_4 AMB
- 175°C maximum junction temperature
- Thermistor inside
- Low Switching Losses

Applications

- xEV Applications
- Motor Drives
- Vehicle Fast Chargers
- Smart-Grid/Grid-Tied Distributed Generation

Circuit diagram

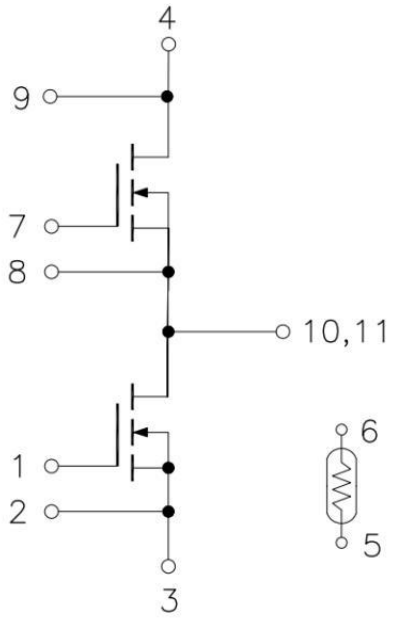

Figure 1. Out drawing & circuit diagram for DFS900HF12I4C1

Pin Configuration and Marking Information

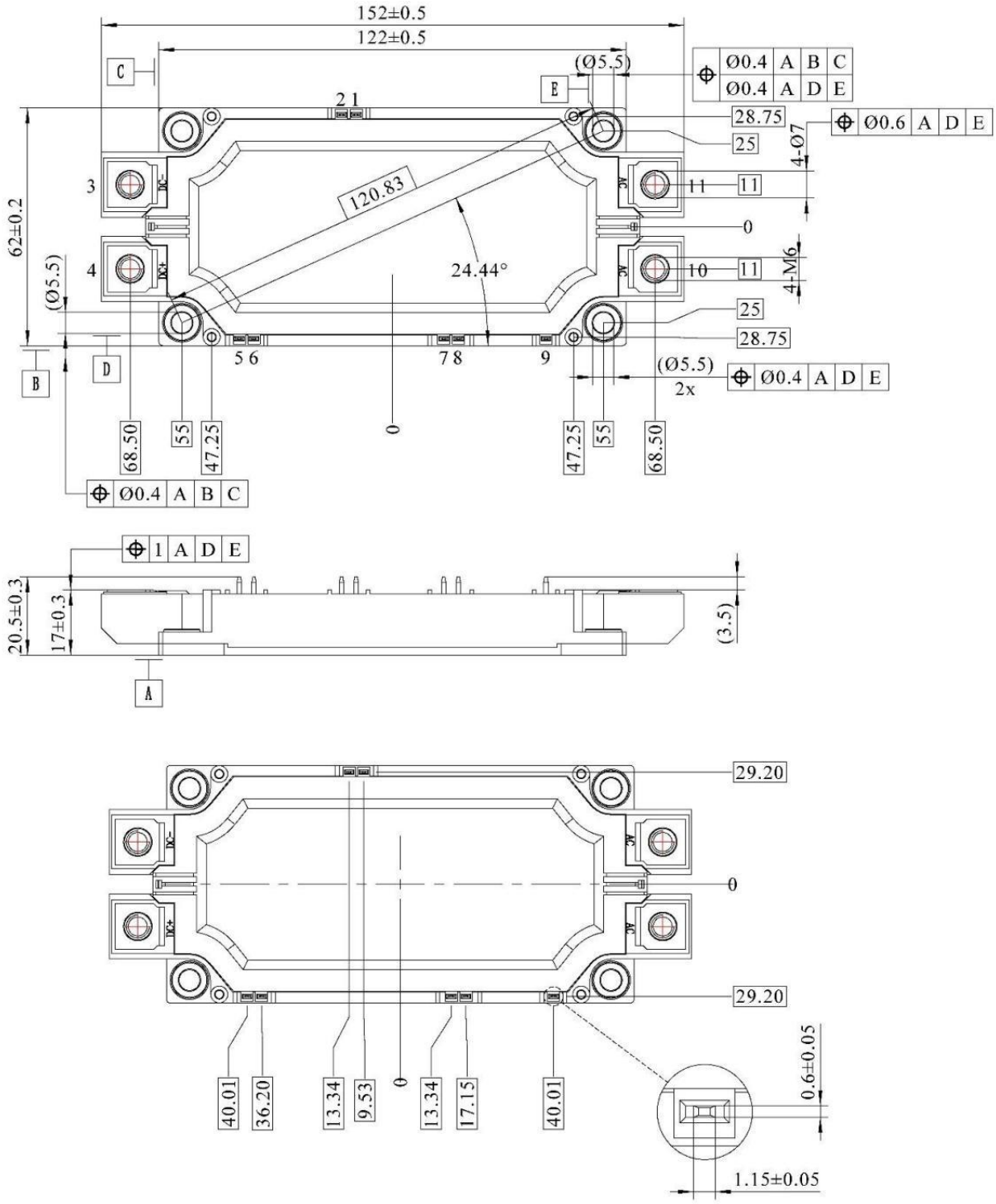

Figure 2. Pin configuration

DFS900HF12I4C1

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Module

Parameter	Condition	Value	Unit
Isolation Voltage	RMS, f =50Hz, t =1min	3.4	kV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 13	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	>400	-
Module lead resistance, terminals–chip	T_C =25°C	0.5	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	340	g

Maximum Ratings (T_j =25°C unless otherwise specified)

Symbol	Parameter	Condition	Ratings	Unit
V_{DSS}	Drain-Source Voltage	G-S Short	1200	V
V_{GSS}	Gate-Source Voltage	D-S Short, AC frequency ⩾1Hz, Note1	-10 to 22	V
I_{DS}	DC Continuous Drain Current	T_C =25°C, V_{GS} =18V	1000	A
I_{DS}	DC Continuous Drain Current	T_C =60°C, V_{GS} =18V	900	A
I_{SD}	Source (Body diode) Current	T_C =25°C, with ON signal	1000	A
I_{SD}	Source (Body diode) Current	T_C =60°C, with ON signal	900	A
I_{DSM}	Pulse Forward Current	T_C =25°C, Pulse width =1ms, V_{GS} =20V, Note2	1800	A
P_{tot}	Total Power Dissipation	T_C =25°C	3000	W
T_{jmax}	Max Junction Temperature	-	175	°C
T_{stg}	Storage Temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, +18V/-5V ,+18V/-4V, +15V/-4V

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R_{25}	Resistance	T_C =25°C	-	5	-	kΩ
ΔR/R	Deviation of R_{100}	T_C =100°C, R_{100} =493Ω	-5	-	5	%
P_{25}	Power dissipation	T_C =25°C	-	-	20	mW
$B_{25/50}$	B-value	R2 =R25 exp [$B_{25/50}$(1/T2 - 1/(298,15 K))]	-	3375	-	K
$B_{25/80}$	B-value	R2 =R25 exp [$B_{25/80}$(1/T2 - 1/(298,15 K))]	-	3411	-	K
$B_{25/100}$	B-value	R2 =R25 exp [$B_{25/100}$(1/T2 - 1/(298,15 K))]	-	3433	-	K

MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} =0V, I_D =900μA		1200	-	-	V
I_{DSS}	Zero gate voltage drain Current	V_{DS}=1200V, V_{GS}=0V	T_j =25°C	-	1.17	200	μA
			T_j=150°C		36.97	200	
$V_{GS(th)}$	Gate-source threshold Voltage	I_D=315mA V_{DS}=V_{GS}	T_j =25°C	1.8	2.89	3.6	V
			T_j=150°C	1.5	2.1	3.6	
I_{GSS}	Gate-Source Leakage Current	V_{GS} =20V, V_{DS} =0V	T_j =25°C	-	2.35	900	nA
			T_j=150°C	-	145.7	900	
$R_{DS(on)}$	Static drain-source On-state resistance	I_D=900A V_{GS}=+15V	T_j=25°C	-	3.0	3.3	mΩ
			T_j=150°C	-	3.93	4.3	
$V_{DS(on)}$	Static drain-source On-state Voltage	I_D=900A V_{GS}=+15V	T_j=25°C	-	2.73	-	V
			T_j=150°C	-	3.46	-	
C_{iss}	Input Capacitance	V_D=1000V, V_{GS}=0V f=200kHz, V_{AC}=25mV		-	52.2	-	nF
C_{oss}	Output Capacitance			-	1.60	-	
C_{rss}	Reverse transfer Capacitance			-	0.13	-	
R_{Gint}	Internal gate resistor	-		-	0.7	-	Ω
Q_G	Total gate charge	V_{DD}=800V, I_D=540A, V_{GS}=+18/-4V		-	1890	-	nC
$t_{d(on)}$	Turn-on delay time	V_{DD}=600V I_D=900A V_{GS}=+18/-4V R_g=5.1Ω Inductive load switching operation	T_j=25°C	-	0.223	-	μs
			T_j=150°C	-	0.193	-	
t_r	Rise time		T_j=25°C	-	0.162	-	μs
			T_j=150°C	-	0.132	-	
$t_{d(off)}$	Turn-off delay time		T_j=25°C	-	0.441	-	μs
			T_j=150°C	-	0.549	-	
t_f	Fall time		T_j=25°C	-	0.11	-	μs
			T_j=150°C	-	0.136	-	
E_{on}	Turn-on power dissipation		T_j=25°C	-	76.39	-	mJ
			T_j=150°C	-	62.52	-	

E_{off}	Turn-off power dissipation		T_j =25°C	-	70.99	-	mJ
			T_j =150°C	-	73.49	-	
$R_{th(j-c)}$	FET Thermal Resistance	Junction to Case		-	0.05	-	K/W
$R_{th(c-f)}$	Contact thermal Resistance	With thermal conductive grease, Note3		-	0.015	-	K/W

Note3: Assumes Thermal Conductivity of grease is 0.9W/m ▪ K and thickness is 50um.

Body Diode Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_{SD}	Body Diode Forward Voltage	V_{GS} =-5V I_{SD} =900A	T_j =25°C	5.0	5.53	7.0	V
			T_j =175°C	4.0	5.04	6.0	
T_{rr}	Reverse recovery time	V_{DD} =600V I_D =900A V_{GS} =+18/-4V R_g =5.1Ω Inductive load switching operation	T_j =25°C	-	0.048	-	μs
			T_j =150°C	-	0.66	-	
Q_{rr}	Reverse recovery charge		T_j =25°C	-	3.64	-	uC
			T_j =150°C	-	8.35	-	
E_{rr}	Diode switching power dissipation		T_j =25°C	-	0.42	-	mJ
			T_j =150°C	-	1.11	-	

Test Conditions

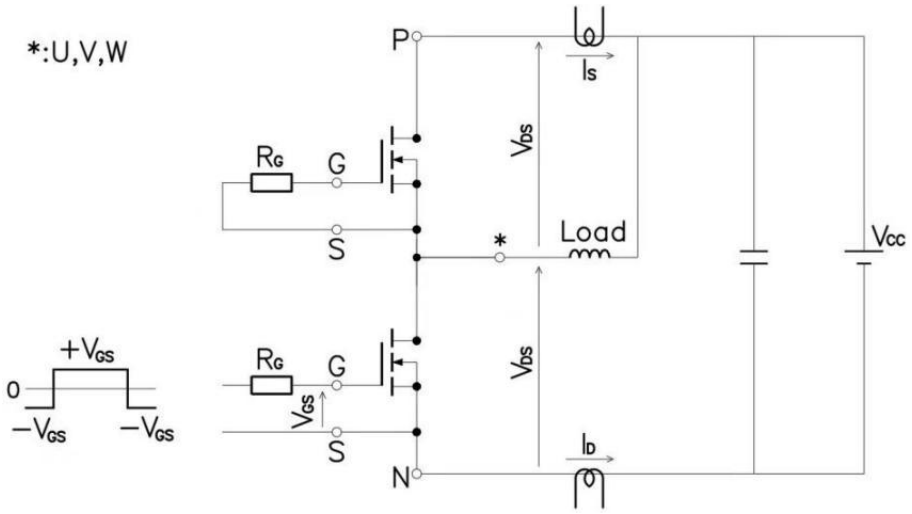

Figure 3. Switching time measure circuit

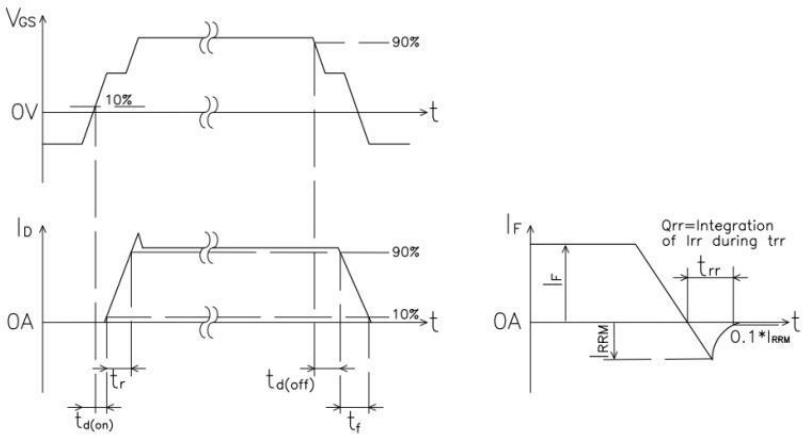

Figure 4. Switching time definition

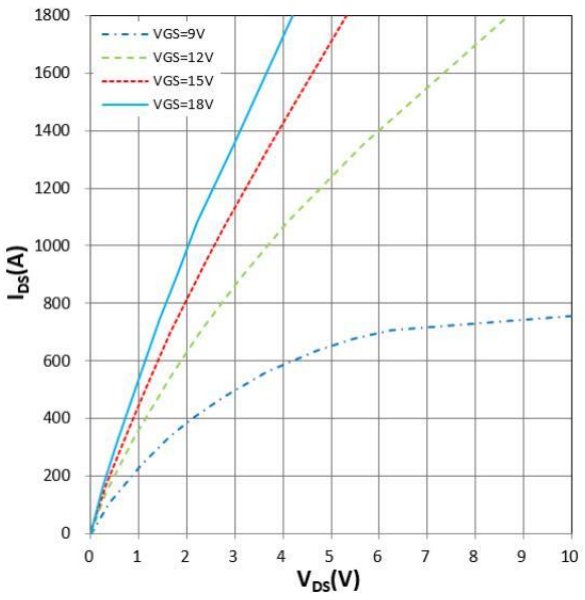

Figure 5. I_{DS} vs V_{DS}

T_j =25°C

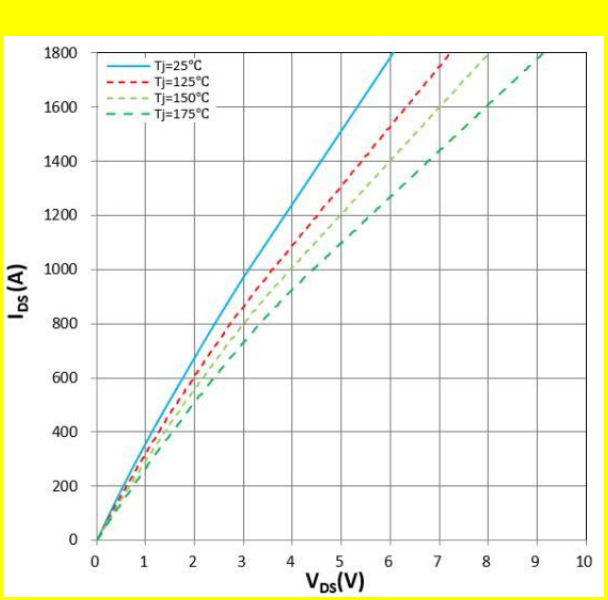

Figure 6. I_{DS} vs V_{DS}

V_{GS} =15V

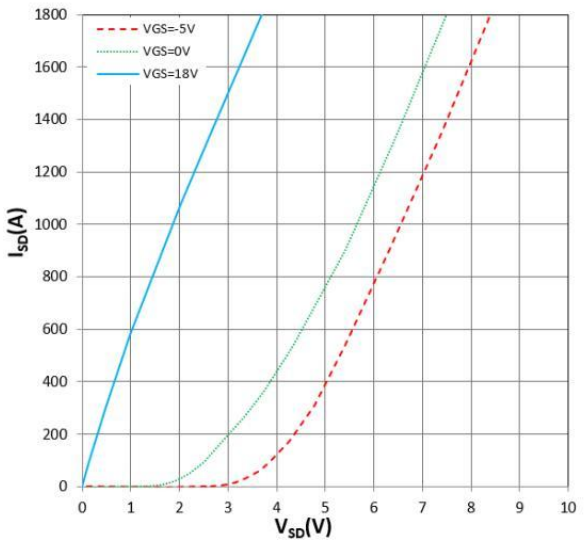

Figure 7. I_{SD} vs V_{SD}

T_j =25°C

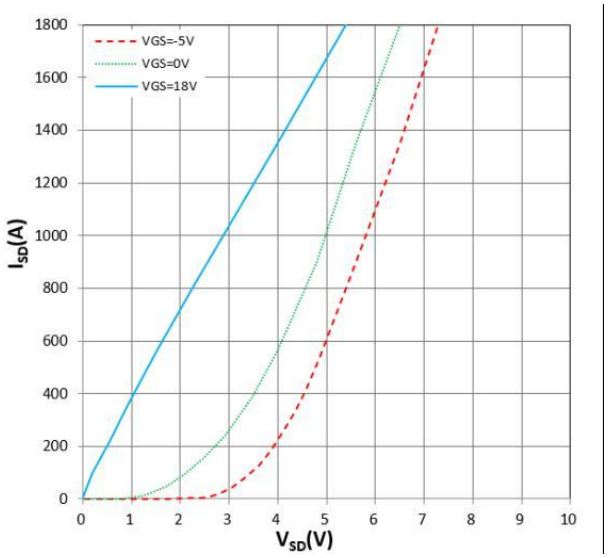

Figure 8. I_{SD} vs V_{SD}

T_j =175°C

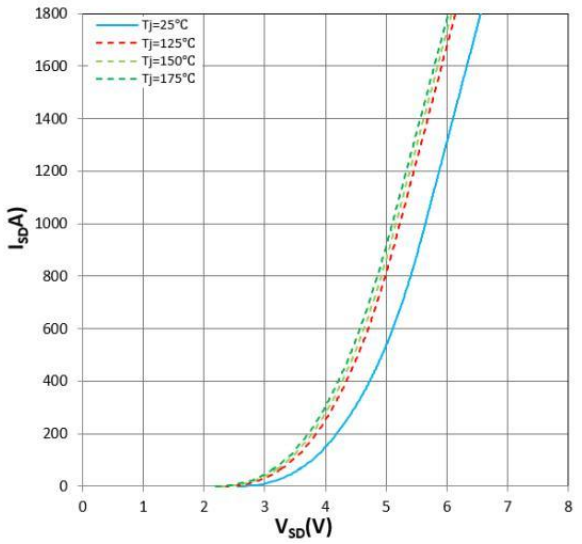

Figure 9. I_{SD} vs V_{SD}

V_{GS}=-5V

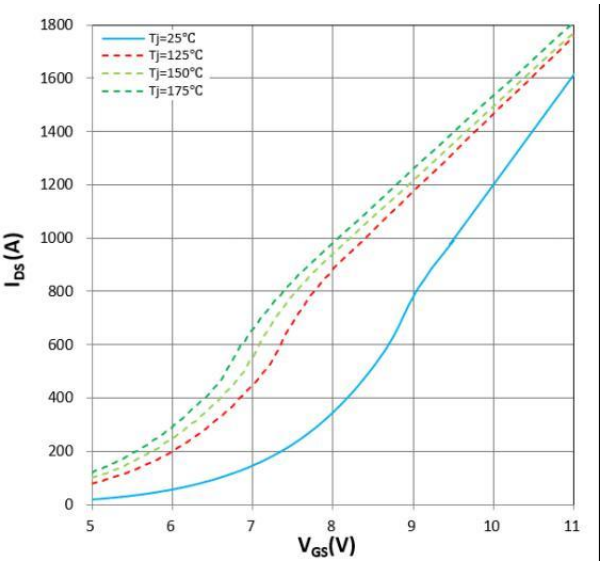

Figure 10. I_{DS} vs V_{GS}

V_{DS}=20V

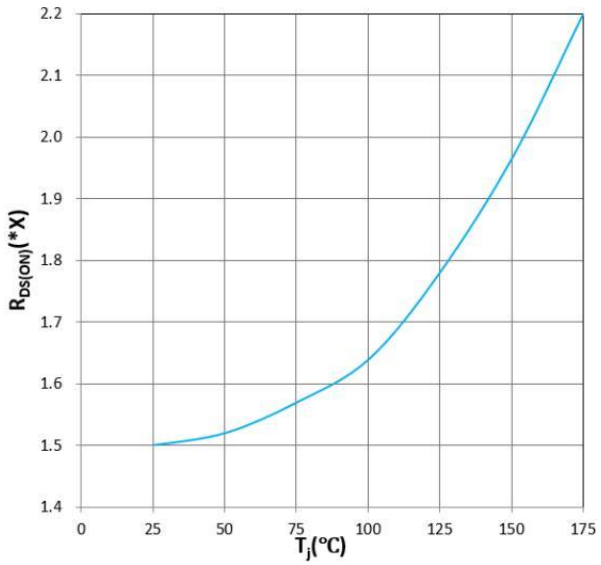

Figure 11. $R_{DS(ON)}$ vs T_j

V_{GS} =+15V, I_D =900A, 1.0X =2.0mΩ

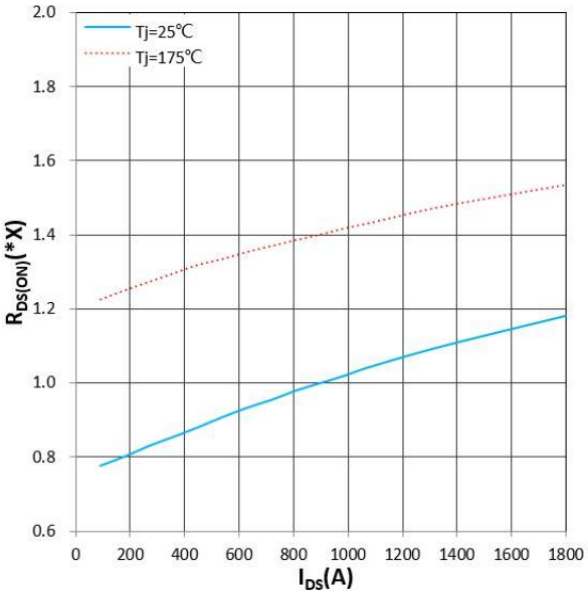

Figure 12. $R_{DS(ON)}$ vs I_{DS}

T_j =25℃/175℃, V_{GS} =+15V, 1.0X =2.0mΩ

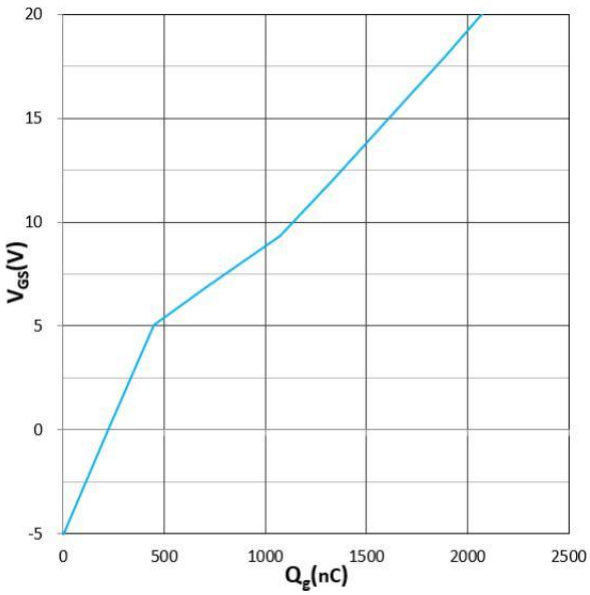

Figure 13. V_{GS} vs Q_g

T_j =25℃, V_{DS} =800V, I_D=540A

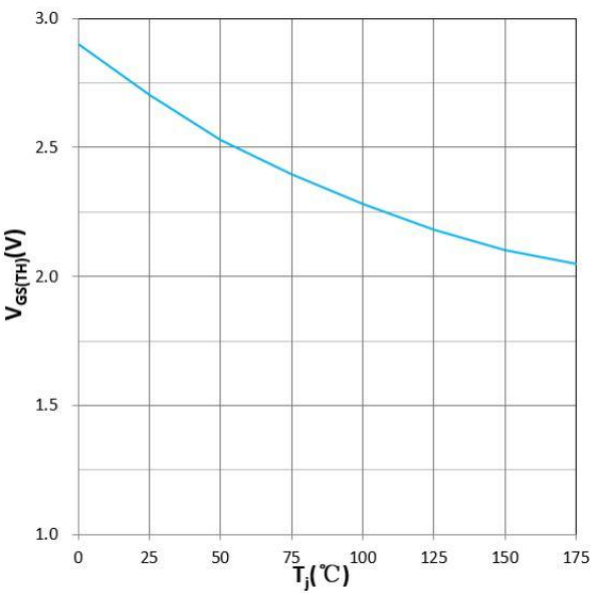

Figure 14. $V_{GS(TH)}$ vs T_j

V_{GS}=V_{DS} , I_D=315mA

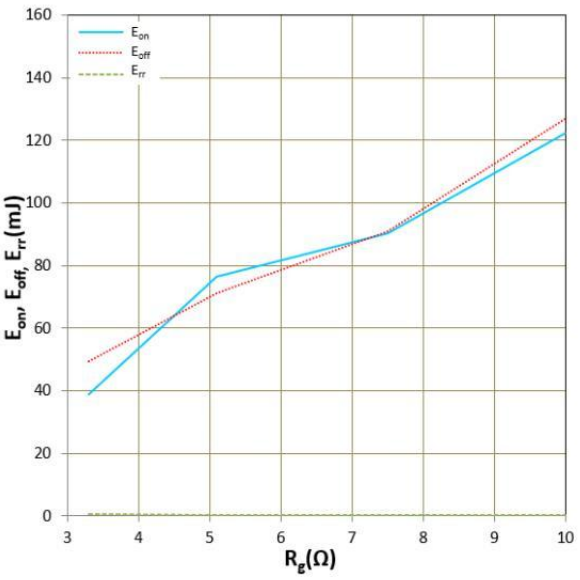

Figure 15. E_{on}, E_{off}, E_{rr} vs R_g

T_j=25°C, V_{DD}=600V, V_{GS}=+18V/-4V, I_D=900A

Inductive Load

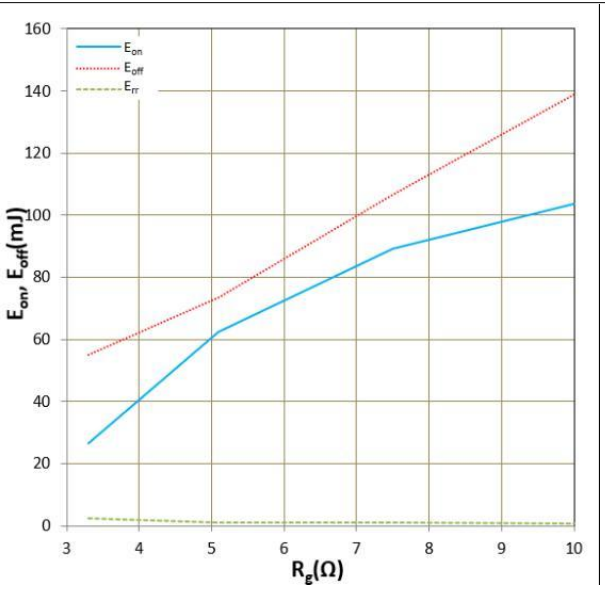

Figure 16. E_{on}, E_{off} , E_{rr} vs R_g

T_j=150°C, V_{DD}=600V, V_{GS}=+18V/-4V, I_D=900A

Inductive Load

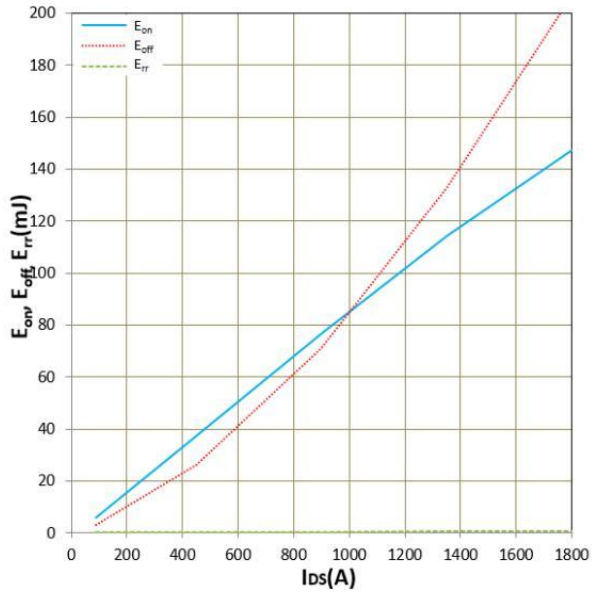

Figure 17. E_{on}, E_{off}, E_{rr} vs I_D

T_j=25°C, V_{DD}=600V, V_{GS}=+18V/-4V,

R_g =5.1Ω, Inductive Load

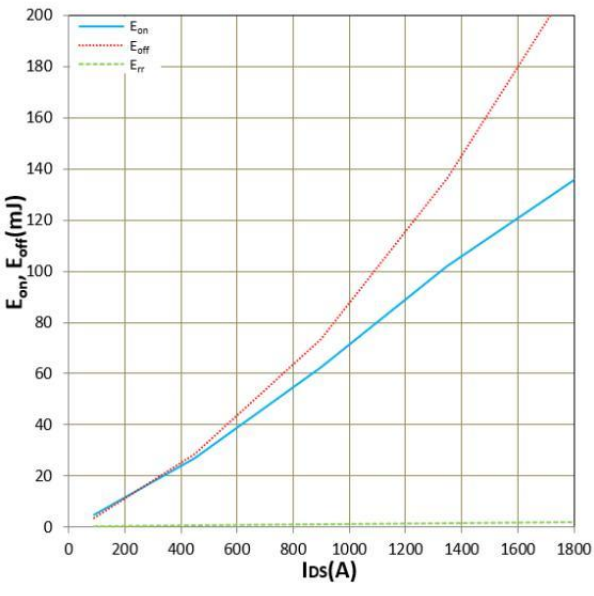

Figure 18. E_{on}, E_{off}, E_{rr} vs I_D

T_j=150°C, V_{DD}=600V, V_{GS}=+18V/-4V,

R_g =5.1Ω, Inductive Load

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Editing record：

Version	Content	Data	Editor	Approver
1.0	Update dynamic and static value	2025.05.13	Congqing.Cao	